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(54) **PACKAGED SEMICONDUCTOR COMPONENTS HAVING SUBSTANTIALLY RIGID SUPPORT MEMBERS AND METHODS OF PACKAGING SEMICONDUCTOR COMPONENTS**

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See application file for complete search history.

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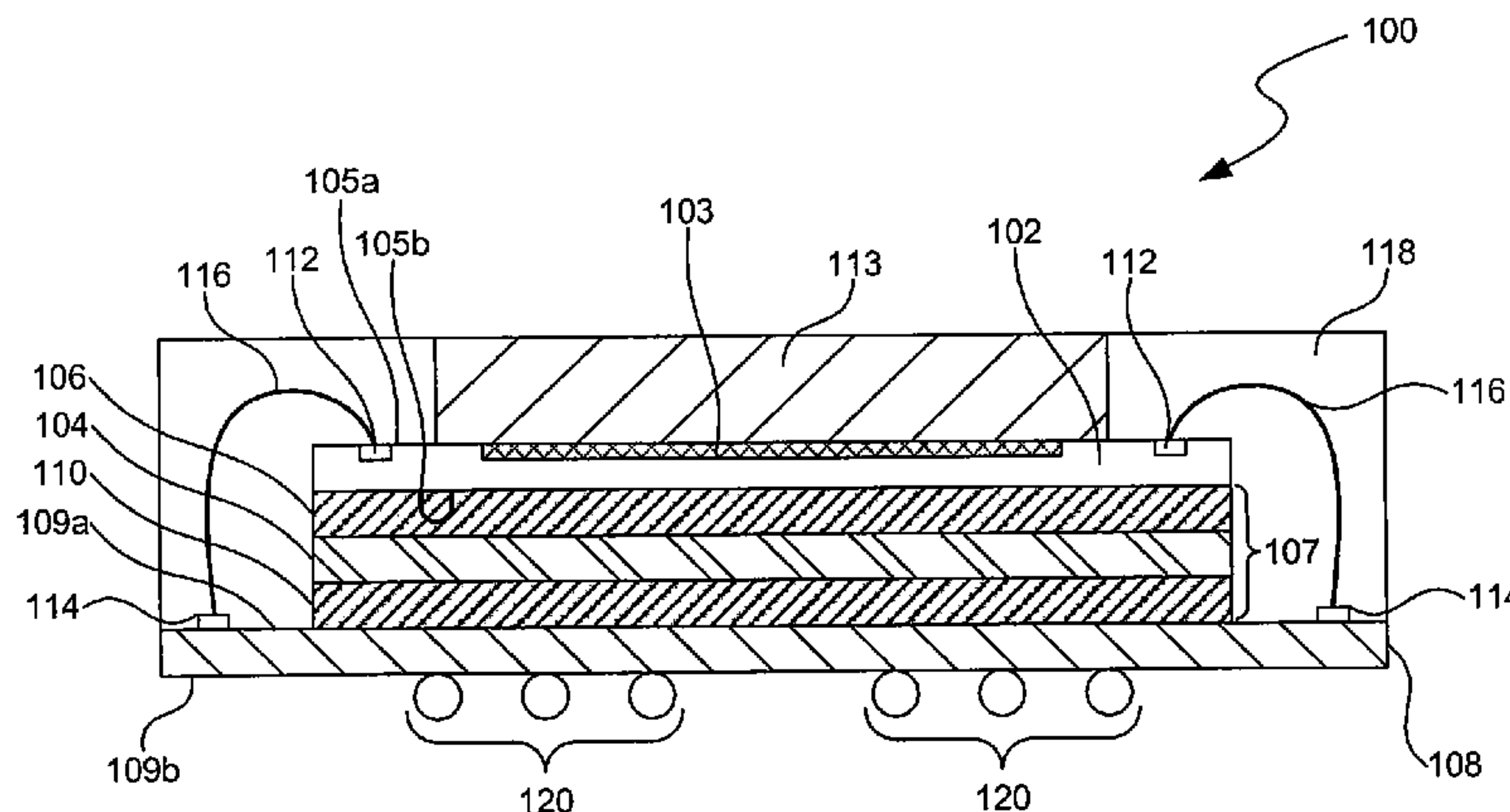
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(57) **ABSTRACT**

Packaged semiconductor components having substantially rigid support member are disclosed. The packages can include a semiconductor die and a support member proximate to the semiconductor die. The support member is at least substantially rigid. The packages can further include an adhesive between the support member and the semiconductor die and adhesively attaching the support member to the semiconductor die. The packages can also include a substrate carrying the semiconductor die and the support member attached to the semiconductor die.

15 Claims, 5 Drawing Sheets



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Page 2

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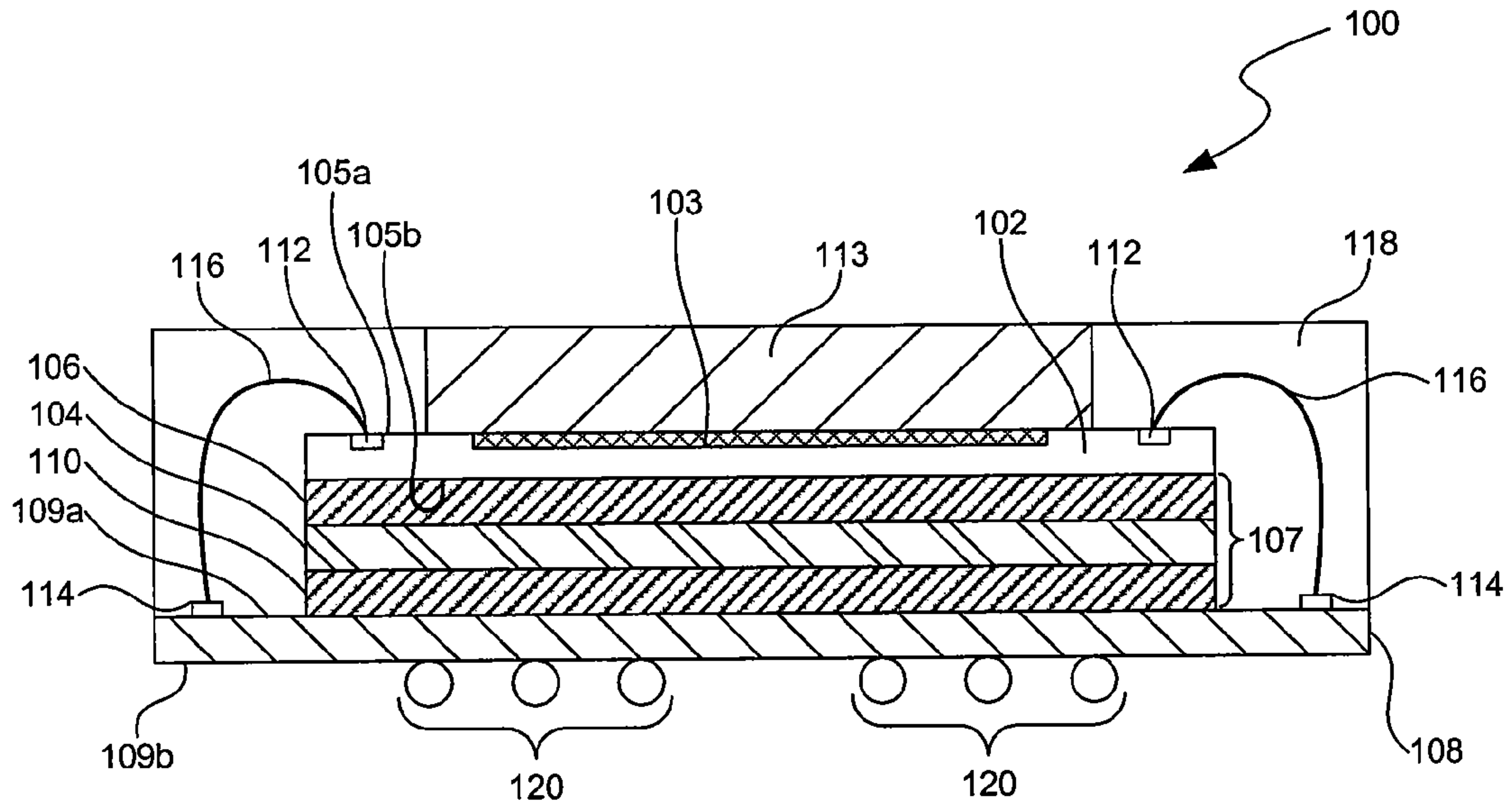


FIG. 1

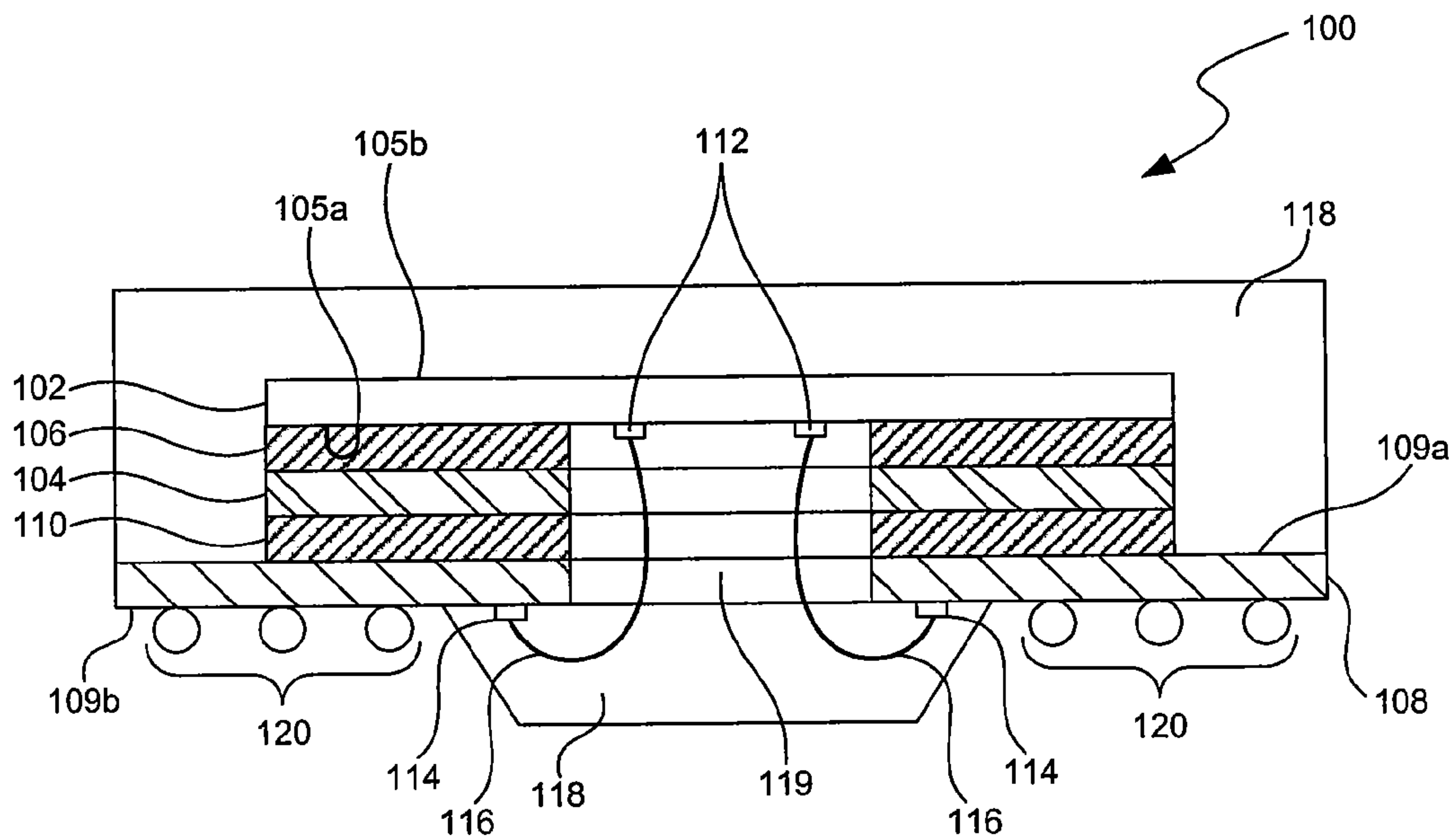


FIG. 3

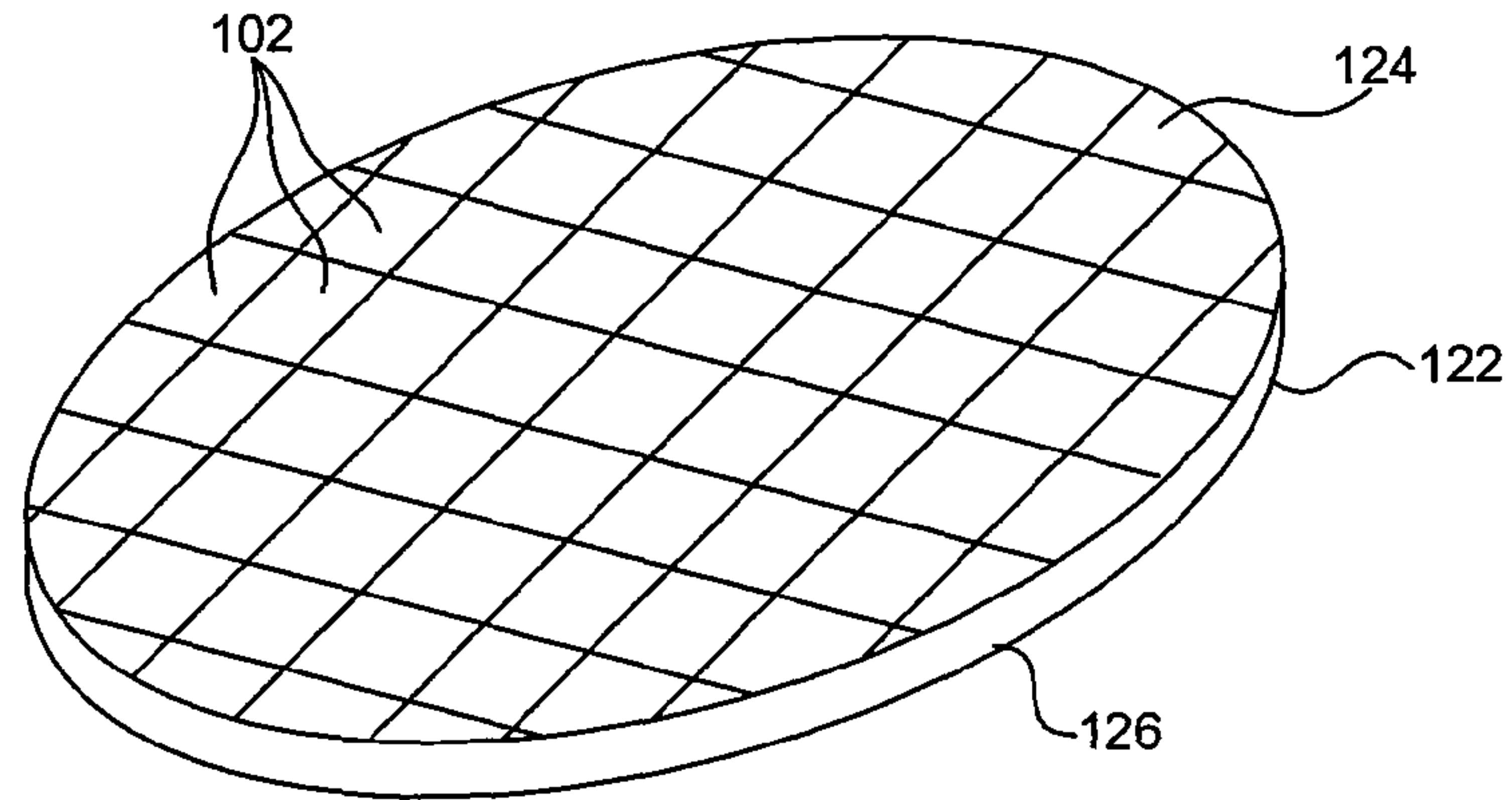


FIG. 2A

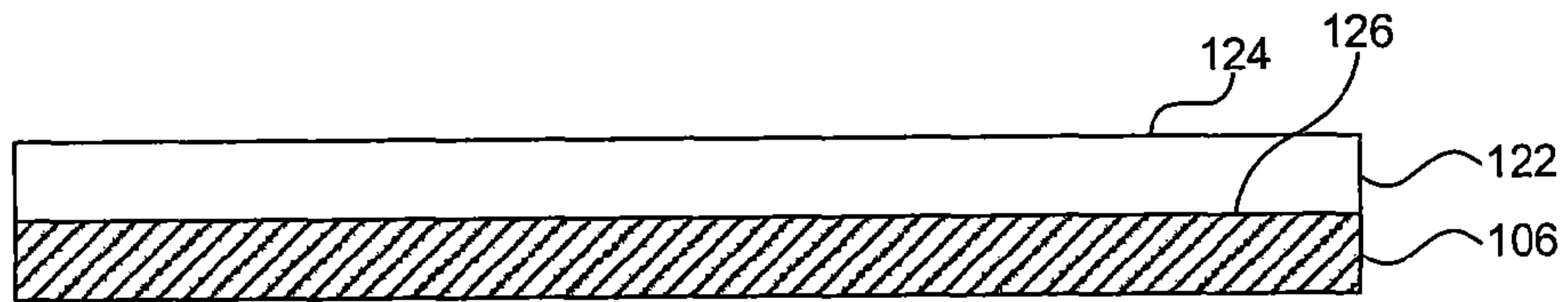


FIG. 2B

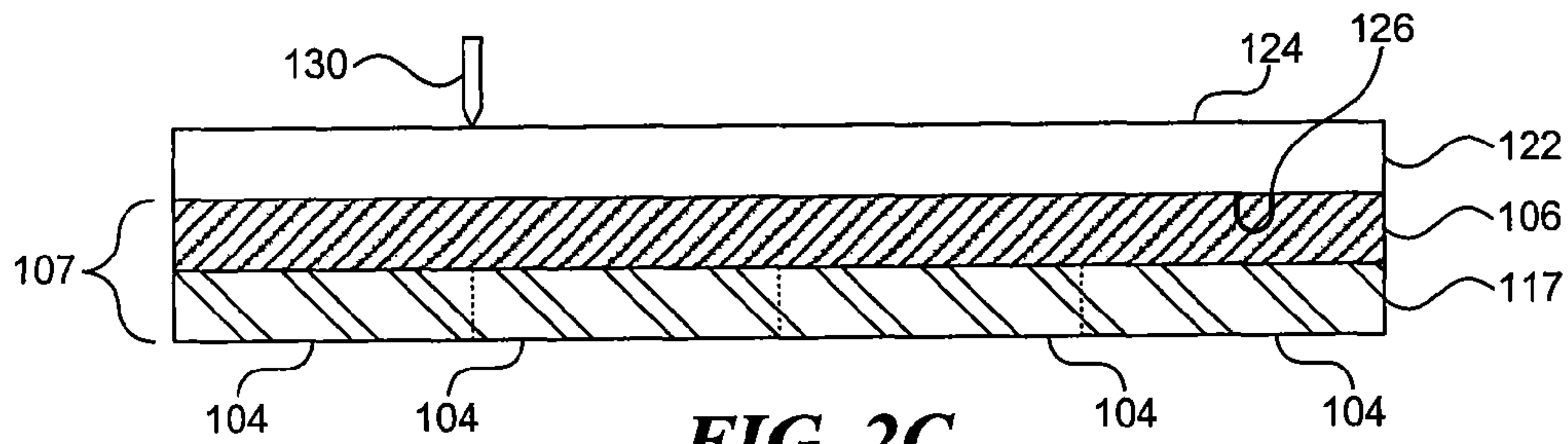


FIG. 2C

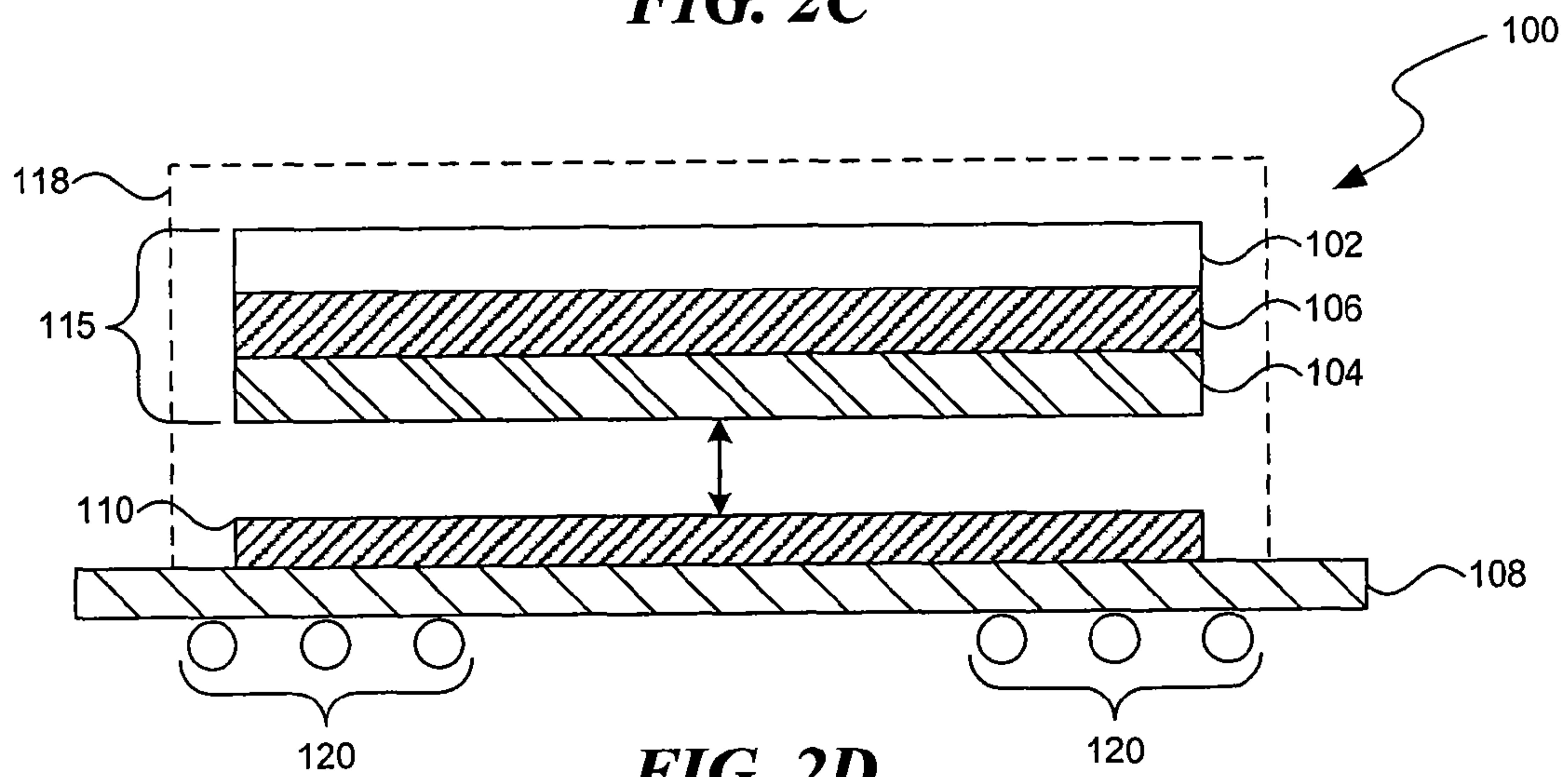


FIG. 2D

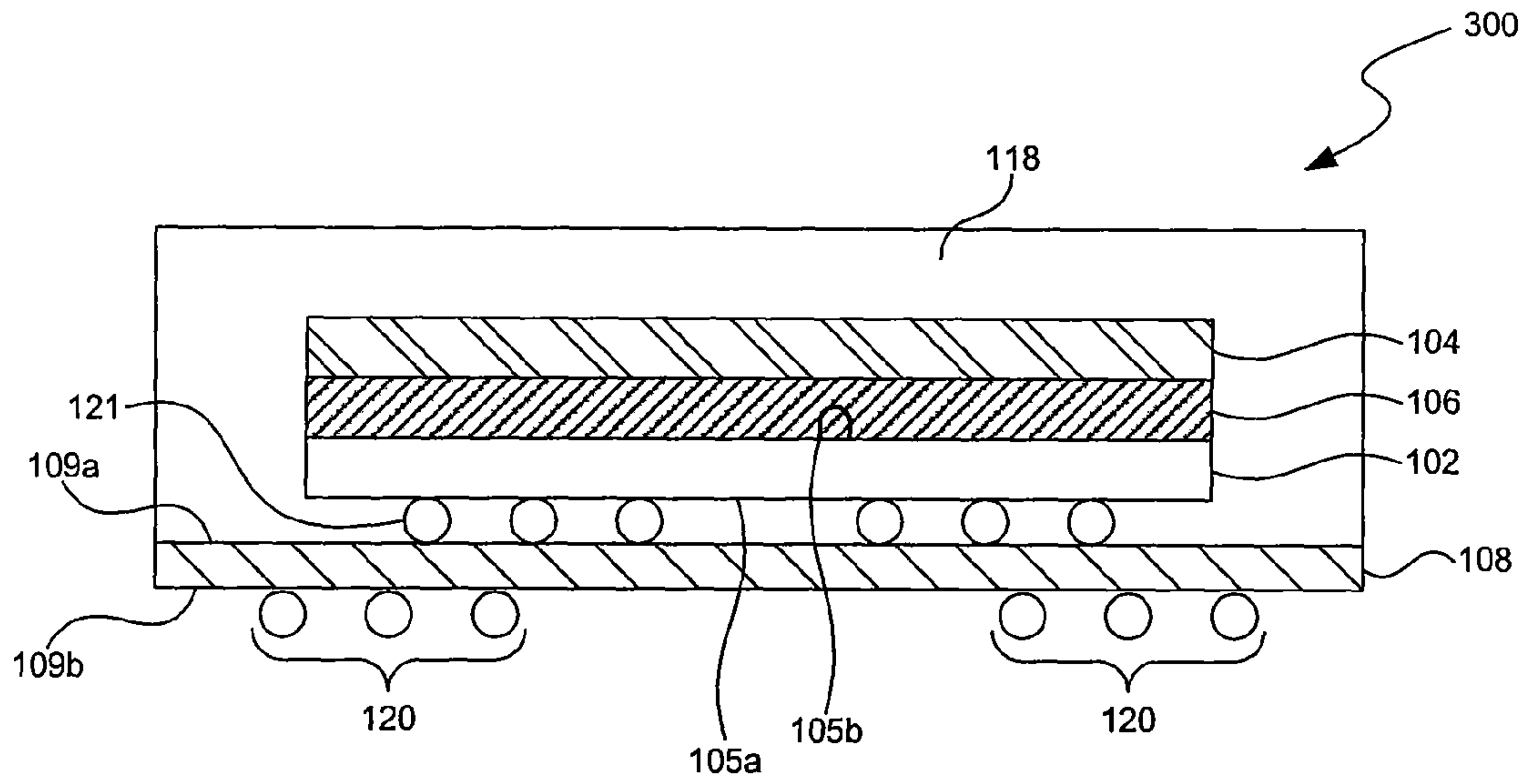


FIG. 4

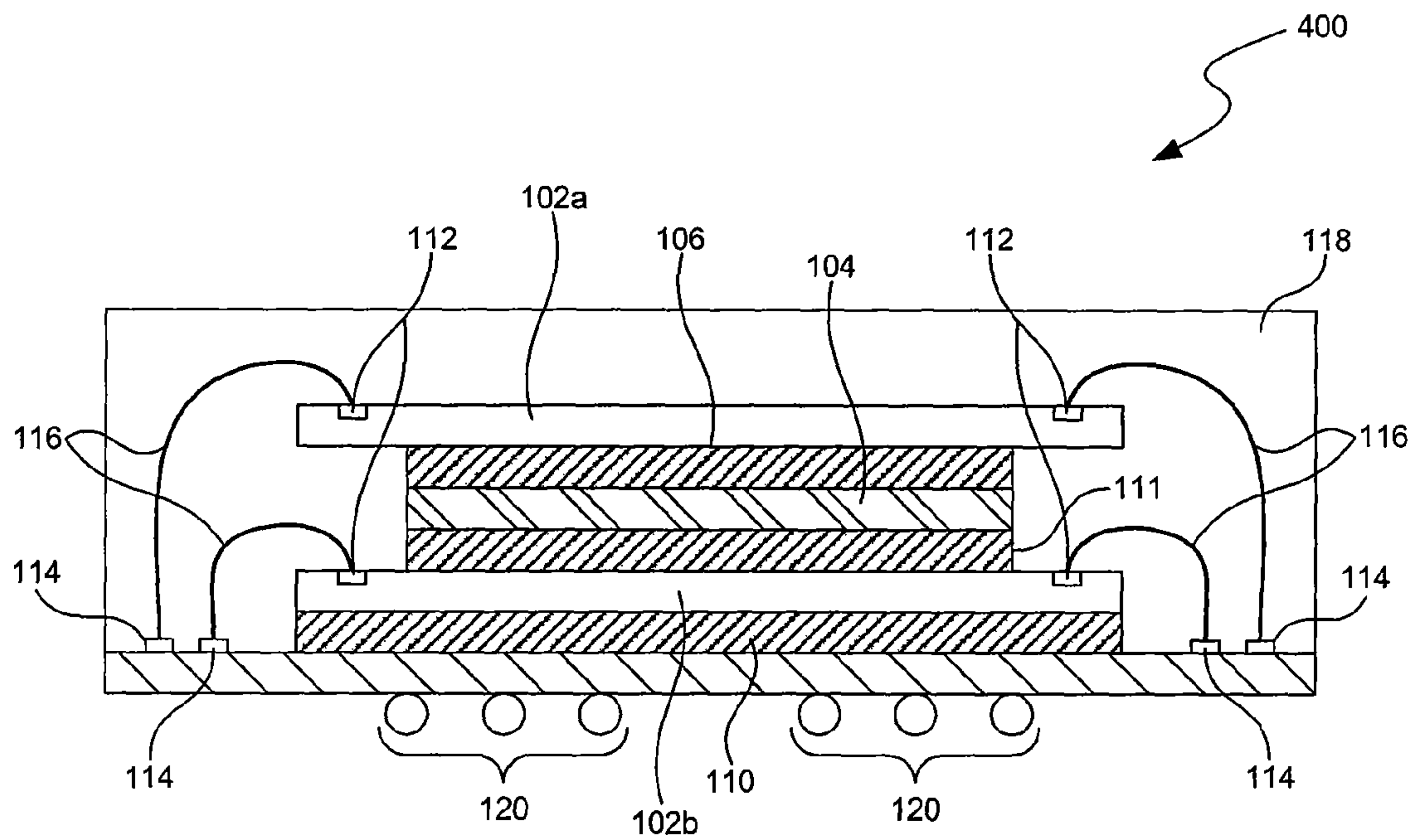


FIG. 5

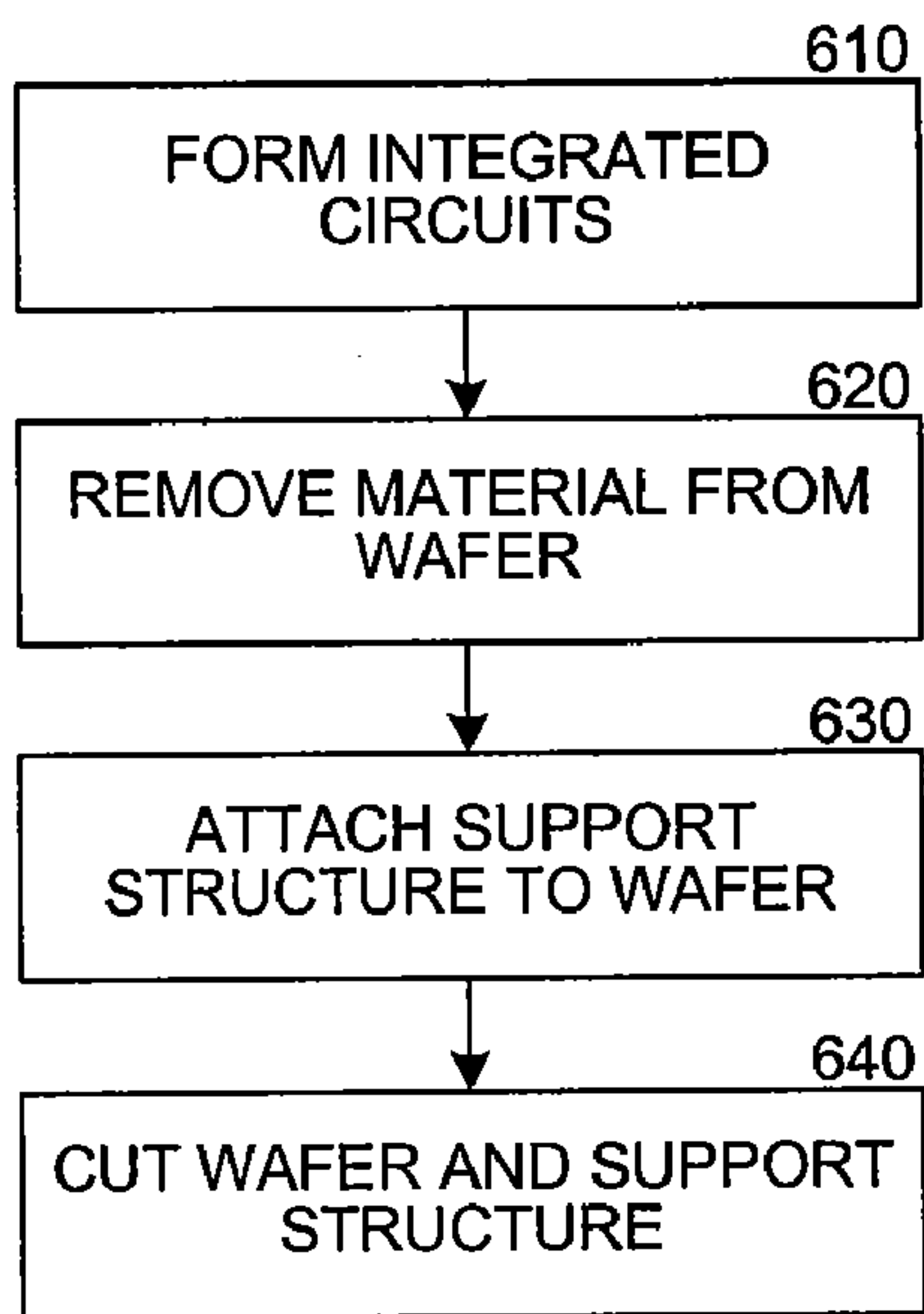


FIG. 6

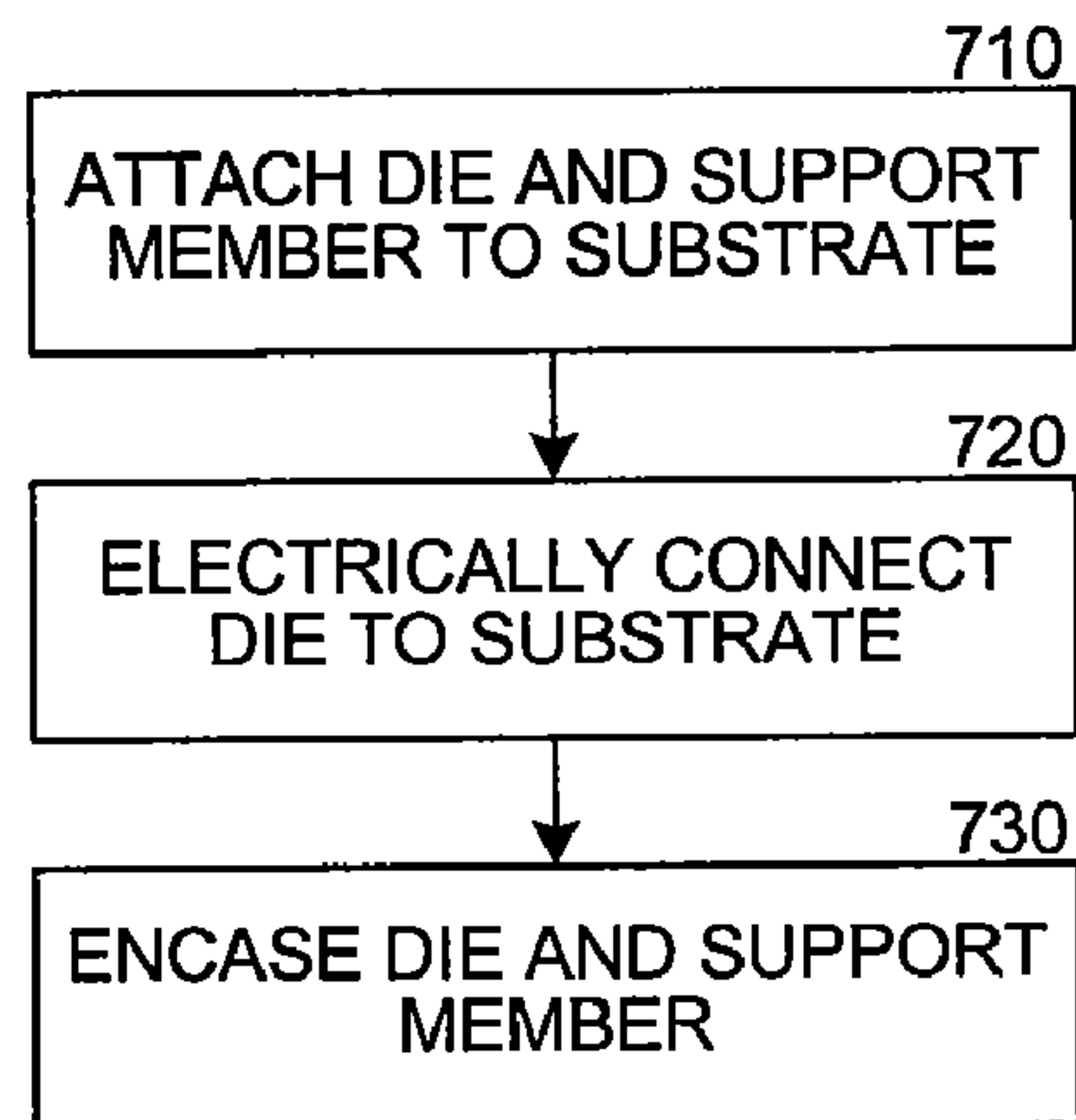


FIG. 7

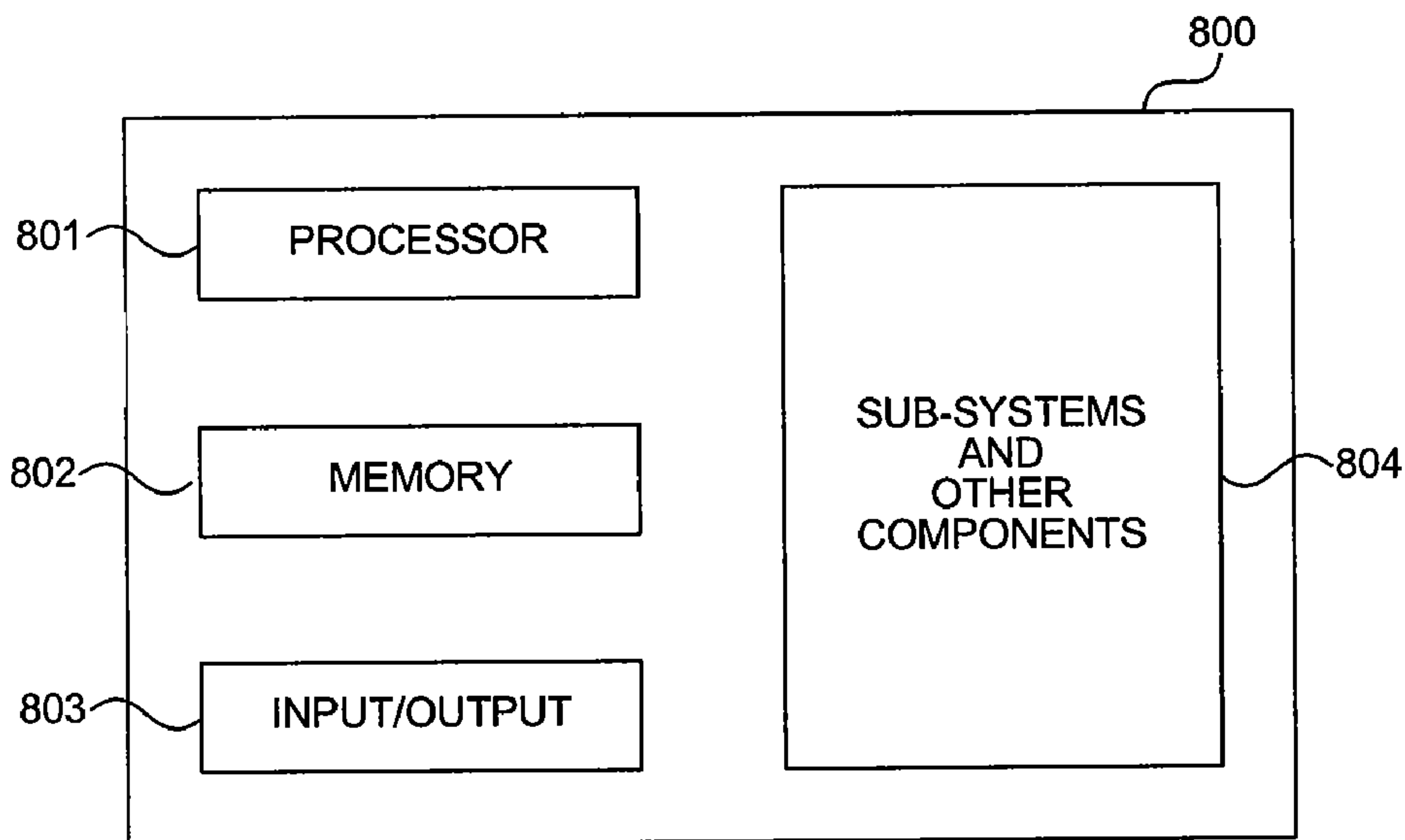


FIG. 8

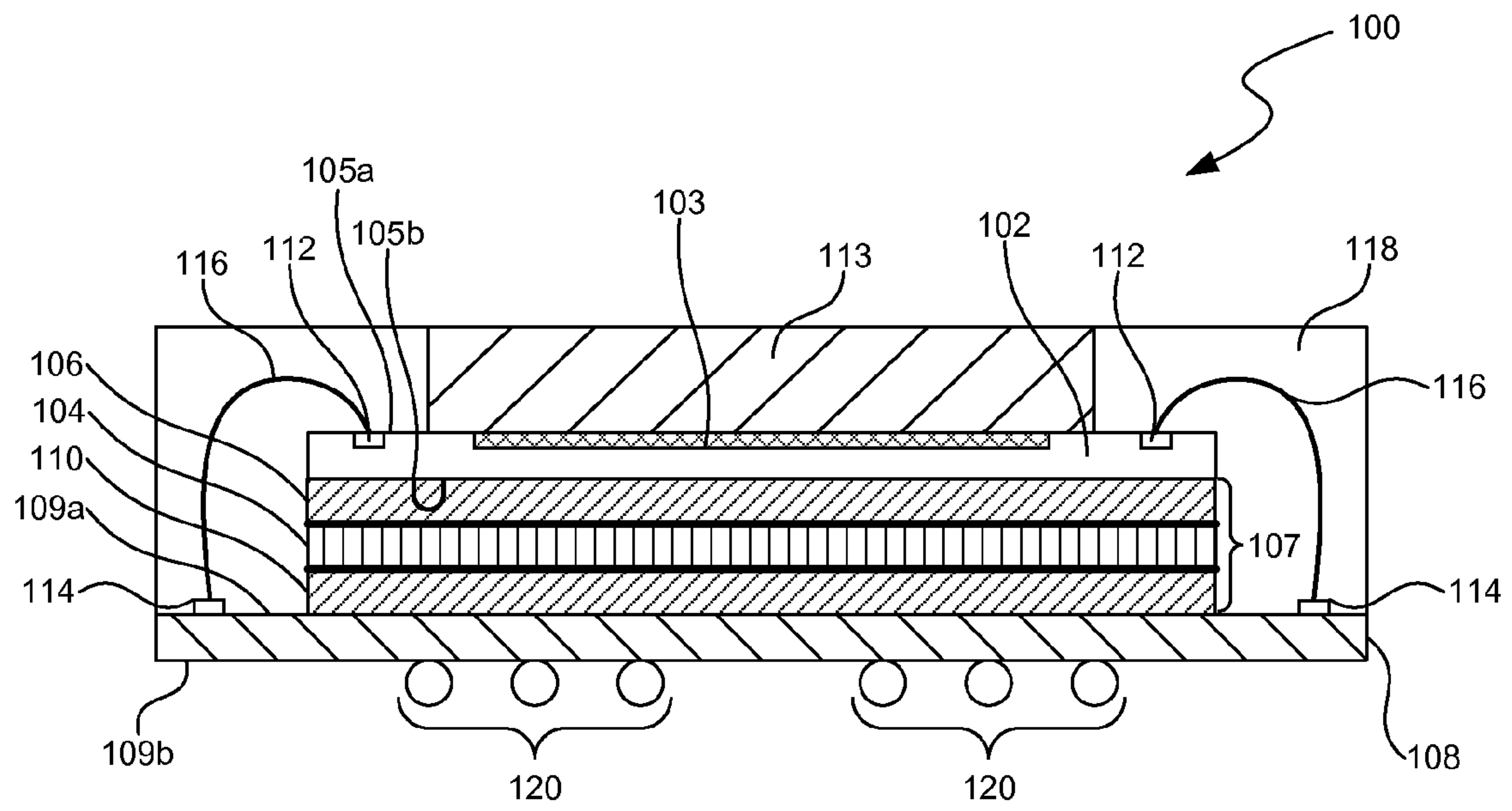


FIG. 9

1

**PACKAGED SEMICONDUCTOR
COMPONENTS HAVING SUBSTANTIALLY
RIGID SUPPORT MEMBERS AND METHODS
OF PACKAGING SEMICONDUCTOR
COMPONENTS**

TECHNICAL FIELD

The present disclosure is related to packaged semiconductor components and methods for assembling or packaging semiconductor components.

BACKGROUND

Semiconductor devices are typically manufactured on semiconductor wafers or other types of workpieces using sophisticated equipment and processes that enable reliable, high-quality manufacturing. The individual dies (e.g., devices) generally include integrated circuits and a plurality of bond-pads coupled to the integrated circuits. The bond-pads provide external contacts through which supply voltage, electrical signals, and other input/output parameters are transmitted to/from the integrated circuits. The bond-pads are usually very small, and they are typically arranged in dense arrays having a fine pitch between bond-pads. The wafers and dies can also be quite delicate. As a result, the dies are packaged to protect the dies and to connect the bond-pads to arrays of larger terminals that can be soldered to printed circuit boards.

One challenge of manufacturing semiconductor components is cost effectively packaging the dies. Electronic product manufacturers are under continuous pressure to reduce the size of their products. Accordingly, microelectronic die manufacturers seek to reduce the size of the packaged dies incorporated into the electronic products. One approach to reducing the size of packaged dies is to reduce the thickness of the dies. For example, the backside of a wafer is often ground, etched, or otherwise processed to reduce the thickness of the wafer. After being thinned, the wafer is cut to singulate the dies.

Reducing the thickness of the wafer, however, can cause several manufacturing defects. For example, as the thickness of the wafer decreases, the backside of the wafer is more likely to chip during singulation, at least partially because cracks in the wafer can more readily propagate from one surface to another surface of the wafer. Moreover, if the dies include photodiode, photogate, or other types of photo-sensing devices, then infrared radiation used during lithography processes can potentially damage these photo-sensing devices. Accordingly, there is a need to improve the processing of thinned semiconductor workpieces.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is a schematic side cross-sectional view of a packaged semiconductor component in accordance with an embodiment of the disclosure.

FIGS. 2A-D are perspective and cross-sectional views illustrating stages of a process for manufacturing the packaged semiconductor package of FIG. 1 in accordance with an embodiment of the disclosure.

FIG. 3 is a schematic side cross-sectional view of a packaged semiconductor component in accordance with another embodiment of the disclosure.

FIG. 4 is a schematic side cross-sectional view of a packaged semiconductor component in accordance with a further embodiment of the disclosure.

2

FIG. 5 is a schematic side cross-sectional view of a packaged semiconductor component having stacked semiconductor dies in accordance with an embodiment of the disclosure.

FIG. 6 is a flow chart of a method for fabricating a packaged semiconductor component in accordance with an embodiment of the disclosure.

FIG. 7 is a flow chart of a method for fabricating a packaged semiconductor component in accordance with another embodiment of the disclosure.

FIG. 8 is a schematic view of a system that incorporates a packaged semiconductor component in accordance with embodiments of the disclosure.

FIG. 9 is a schematic side cross-sectional view of a packaged semiconductor component in accordance with an additional embodiment of the disclosure.

DETAILED DESCRIPTION

Specific details of several embodiments of the disclosure are described below with reference to packaged semiconductor components and methods for manufacturing packaged semiconductor components. The semiconductor components are manufactured on semiconductor wafers that can include substrates upon which and/or in which microelectronic devices, micromechanical devices, data storage elements, optics, read/write components, and other features are fabricated. For example, SRAM, DRAM (e.g., DDR/SDRAM), flash-memory (e.g., NAND flash-memory), processors, imagers, and other types of devices can be constructed on semiconductor wafers. Although many of the embodiments are described below with respect to semiconductor devices that have integrated circuits, other embodiments include other types of devices manufactured on other types of substrate. Moreover, several other embodiments of the invention can have different configurations, components, or procedures than those described in this section. A person of ordinary skill in the art, therefore, will accordingly understand that the invention can have other embodiments with additional elements, or the invention can have other embodiments without several of the features shown and described below with reference to FIGS. 1-8.

FIG. 1 is a schematic side cross-sectional view of a packaged semiconductor component 100 in accordance with an embodiment of the disclosure. The packaged component 100 can include a semiconductor die 102 having a first surface 105a, a second surface 105b, and bond pads 112 at the first surface 105a. The packaged component 100 can further include a support member 104 at the second side 105b of the die 102, and a substrate 108 carrying the semiconductor die 102 and the support member 104. A first adhesive 106 attaches the support member 104 to the second surface 105b of the semiconductor die 102, and a second adhesive 110 attaches the support member 104 to the substrate 108. The packaged component 100 can also have wirebonds 116 electrically connecting the bond pads 112 of the semiconductor die 102 to connection sites 114 at the substrate 108, and an encapsulant 118 encapsulating the semiconductor die 102, the support member 104, and the wirebonds 116.

The semiconductor die 102 can include microelectronic devices, micromechanical devices, data storage elements, optics, read/write components, and other features are fabricated. As described above. For example, SRAM, DRAM (e.g., DDR-SDRAM), flash-memory (e.g., NAND flash-memory), processors, imagers, and other types of devices can be constructed on or in the semiconductor die 102. In the embodiment shown in FIG. 1, the semiconductor die 102 can include an array of photo sensors 103 at or near the first

surface **105a** and a glass member **113** adjacent to the array of photo sensors **103**. The illustrated embodiment of the semiconductor die **102** also includes the peripheral bond pads **112** that are proximate to the edges of the semiconductor die **102**, but in other embodiments, the bond pads **112** can be positioned toward to a central region of the semiconductor die **102** (e.g., as shown in FIG. 3).

The support member **104** is at least substantially rigid and can reinforce the semiconductor die **102**. The support member **104** can have a composition that is different from that of the semiconductor die **102**. For example, the support member **104** can be a plate constructed from a metal, a metal alloy, ceramics, polymers, glass, or other materials with sufficient mechanical strength. The support member **104** can also incorporate slots, channels, apertures, or other surface patterns. In another example, the support member **104** can be a laminated structure having a plurality of layers of different materials, of which at least one is at least substantially rigid. For example, the support member **104** can include a plurality of heat conducting fins sandwiched between two plates to provide improved heat conductance, as shown in FIG. 9. In any of these examples, the support member **104** does not include a semiconductor die.

The support member **104** can have a thickness sufficient to provide enough support to protect the semiconductor die **102** during thinning and subsequent processing but still allows easy cutting during singulation. In one embodiment, the thickness of the support member **104** is about 100 microns to about 3 mm, but in other embodiments, the thickness of the support member **104** can be outside this range.

The support member **104** can be a standalone component, or it can be combined with other components of the packaged semiconductor component **100**. For example, the support member **104** can be a separate element from the first and/or second adhesives **106**, **110** before assembly, or can be preformed into a die attach film **107** with the first and/or second adhesives **106**, **110** before assembly. Applying the die attach film **107** can reduce complexity and manufacturing cost by reducing the number of individual processing steps.

The substrate **108** can be a printed circuit board, a silicon wafer, a glass plate, a ceramic unit, or other structure suitable for carrying the semiconductor die **102** and the support member **104**. The substrate **108** can have a first surface **109a** at which the connection sites **114** are positioned, and a second surface **109b** with external terminals to which a plurality of solder balls **120** (six are shown for illustration purposes) are attached. The solder balls **120** are generally arranged in an array that can be surface mounted to an external device (not shown). The substrate **108** also includes internal circuits (not shown) that electrically connect the connection sites **114** at the first surface **109a** to the solder balls **120** at the second surface **109b**.

FIG. 2A-D are perspective and cross-sectional views illustrating a number of stages of a portion of a process for manufacturing the packaged semiconductor component **100** of FIG. 1. As illustrated in FIG. 2A, integrated circuits (not shown) can be first formed in individual dies **102** on a semiconductor wafer **122** having a first wafer surface **124** and a second wafer surface **126** opposite the first wafer surface **124**. For example, the array of photo sensors **103** (FIG. 1) or other types of electrical, optical, or mechanical devices can be formed in or on the first wafer surface **124** of the semiconductor wafer **122**. The semiconductor wafer **122** is thinned after fabricating the dies **102** by removing material from the second wafer surface **126** via mechanical grinding, chemical-mechanical polishing, wet etching, dry chemical etching, or

other suitable processes. The semiconductor wafer **122** can be thinned to be less than, for example, about 700 microns.

FIG. 2B shows the wafer **122** after the first adhesive **106** has been applied onto the second wafer surface **126**. The first adhesive **106** can be applied by spraying, printing, pressing, or another suitable technique. Referring to FIG. 2C, a support structure **117** is attached to the first adhesive **106** to bind with the semiconductor wafer **122**. The support structure **117** imparts rigidity to the semiconductor wafer **122** and protects the second wafer surface **126** of the wafer **122**. In another embodiment, a preformed die attach film **107** having the first adhesive **106** and the support structure **117** can be applied to the second surface **126** of the semiconductor wafer **122** before cutting.

The semiconductor wafer **122** and the support structure **117** can then be cut into individual semiconductor subassemblies **115** using a saw blade **130**, a laser, or any other suitable cutting techniques. Individual subassemblies **115** can accordingly include the die **102** with the attached support member **104**. The support member **104** is a portion of the overall support structure **117**. As shown in FIG. 2D, individual subassemblies **115** can then be attached to the substrate **108** with the second adhesive **110** and encased with the encapsulant **118** (shown in phantom lines for clarity). In certain embodiments, the subassemblies **115** can also be pre-encapsulated with an encapsulant either similar to or different from the encapsulant **118**, coated with a protective coating (not shown), cleaned, washed, and/or otherwise processed before being attached to the substrate **108**. In other embodiments, the wafer **122** can be cut into individual dies **102** (e.g., singulated) without first being attached with the support structure **117**, and individual support member **104** can be attached to individual dies **102** after singulation.

Several embodiments of the support structure **117** can reduce chipping on the second wafer surface **126** by reinforcing the semiconductor wafer **122** against bending, twisting, or otherwise flexing during cutting. Without being bound by theory, it is believed that contacting the semiconductor wafer **122** with the saw blade **130** can cause micro-cracks in the semiconductor wafer **122**. These micro-cracks can then propagate and join together to form chips along the kerf of the cut. If the semiconductor wafer **122** warps due to its reduced thickness, the warpage can exacerbate the propagation of the micro-cracks and thus cause increased chipping of the semiconductor wafer **122**. As a result, reinforcing the semiconductor wafer **122** with the substantially rigid support structure **117** can reduce the amount of warping and chipping during singulation.

Moreover, several embodiments of the support member **104** can at least partially equalize heat dissipation from various regions of the die **102** when the die is operated. During operation, different regions of the die **102** can have different operating temperatures. For example, regions having logic circuits tend to consume more power than regions having memory elements and thus generate more heat to cause higher operating temperatures. Such temperature variations can cause the packaged component **100** to fail due to thermal stresses. Thus, supporting the die **102** with a support member **104** constructed from a metal, a metal alloy, or other material with sufficient heat conductivity can at least partially equalize the temperatures of different regions of the die **102** and thus improve robustness of the packaged component **100**.

Further, several embodiments of the support member **104** can improve the durability of the packaged component **100** during thermal cycling. During thermal cycling, the die **102** can flex because the die **102** typically has a different coefficient of thermal expansion than the first and/or second adhe-

5

sives **106**, **110**. The flexing of the die **102** can crack the die **102** and/or detach the die **102** from the substrate **108**. Thus, the substantially rigid support member **104** can at least reduce such flexing and thus improve durability of the packaged component **100** during thermal cycling.

Even though the illustrated embodiments described above use adhesives to attach the support member **104** to the die **102** and to the substrate **108**, in other embodiments, the support member **104**, the die **102**, and/or the substrate **108** can be bonded using mechanical fasteners, direct solid-solid bonding techniques, or other fastening techniques. In other embodiments, the support member **104** can be a moldable material (e.g., a resin), and the support member **104** can be attached to the die **102** without an adhesive by first disposing a layer of the moldable material in a molten state on the die **102** and subsequently solidifying the moldable material to form a substantially rigid structure. In further embodiments, the moldable material can at least partially encase the die **102**.

FIG. **3** is a schematic side cross-sectional view of another example of the packaged semiconductor component assembly **100**. Certain aspects of this example and others described herein, are at least generally similar to previously-described examples, and accordingly common acts and structures are identified by the same reference numbers. For purposes of brevity, only selected differences between this example and previous examples are described below. This example, more specifically, is a board-on-chip configuration, in which the semiconductor die **102** includes bond pads **112** located toward a central region of the first surface **105a** of the die **102**, instead of toward the edges of the semiconductor die **102**. The first adhesive **106** attaches the support member **104** to the first surface **105a** of the semiconductor die **102**, and the second adhesive **110** attaches the support member **104** to the substrate **108**. The support member **104**, the adhesives **106**, **110**, and the substrate **108** include apertures that are generally aligned to form an opening **119** that is generally aligned with the centrally located bond pads **112**. The opening **119** can allow the wirebonds **116** to electrically connect the bond pads **212** to the connection sites **114** on the second surface of the substrate **108**. The encapsulant **118** fills the opening **119** and covers the wirebonds **116**. In another version of the board-on-chip configuration, the support member **104** can be attached to the second surface **105b** of the die **102**, and the first surface **105a** is attached directly to the substrate **108** with the second adhesive **110**. In this case, the support member **104** does not include an aperture.

FIG. **4** is a schematic side cross-sectional view of another embodiment having a flip-chip arrangement. In this example, a plurality of internal solder balls **121** are disposed between the first surface **105a** of the semiconductor die **102** and the first surface **109a** of the substrate **108** to electrically connect integrated circuits (not shown) in the semiconductor die **102** to the substrate **108**. The second adhesive **110** (FIG. **3**) is omitted. The first adhesive **106** attaches the support member **104** to the second surface **105b** of the semiconductor die **102**.

FIG. **5** is a schematic side cross-sectional view of a packaged semiconductor component **400** having stacked semiconductor dies **102a-b** in accordance with an embodiment of the disclosure. The semiconductor dies **102a-b** can be generally similar to the semiconductor die **102** in FIG. **1**. The support member **104** separates the first die **102a** and the second die **102b** in a spaced apart arrangement. The first adhesive **106** attaches the support member **104** to the first die **102a**, and the second adhesive **110** attaches the second die **102b** to the substrate **108**. The package **400** can also have a third adhesive **111** attaching the support member **104** to the second die **102b**,

6

and wirebonds **116** electrically connecting the bond pads **112** of the first and second dies **102a-b** to connection sites **114** located on the substrate **108**.

In one embodiment, the support member **104** is a metal (or metal alloy) spacer having a thickness sufficient to allow the bond pads **112** of the first and second dies **102a-b** to be wirebonded to the connection sites **114**. The metal spacer can reduce manufacturing costs for packaging semiconductor dies compared to conventional silicon spacers that are typically used to provide clearance between the first and second dies **102a-b**. More specifically, the silicon spacers can be relatively expensive to manufacture and are relatively brittle. Thus, replacing the silicon spacer with a metal spacer can reduce the unit cost of the packaged semiconductor component **400** and provide a more robust package. Further, the metal spacer can improve heat dissipation of the first and/or second semiconductor dies **102a-b** because the metal spacer typically has a higher heat conductance than a silicon spacer.

FIG. **6** is a flow chart of an embodiment of a method **600** for manufacturing semiconductor components. The method **600** includes forming integrated circuits on a semiconductor wafer (Block **610**), and removing material from a surface of the semiconductor wafer (Block **620**). The method **600** continues by attaching a support structure to the semiconductor wafer (Block **630**). The support structure is at least substantially rigid and has a thickness that allows for easy cutting. Particular techniques for attaching the support structure to the wafer can be selected based on the particular application. The method **600** also includes cutting the semiconductor wafer and the attached support structure into individual dies and attached support members (Block **640**). Individual semiconductor subassemblies having a semiconductor die and a portion of the substantially rigid support structure are thus formed after cutting through the wafer and the support structure. In other embodiments, the semiconductor wafer and the support structure can be separately pre-cut into individual dies and support members before the support member is attached to a corresponding die.

FIG. **7** is a flow chart of an embodiment of a method **700** for packaging semiconductor components. The method **700** includes attaching a semiconductor die and a support member attached to the semiconductor die to a substrate (Block **710**). Adhesives or other suitable fasteners can be used to attach the semiconductor die and the support member to the substrate. The support member is at least substantially rigid. The method also include electrically connecting individual bond pads at the semiconductor die to individual connection sites at the substrate (Block **720**). For example, wirebonds or a plurality of solder balls can electrically connect individual bond pads at the semiconductor die to individual connection sites at the substrate. The method **700** also includes encasing the semiconductor die and the support member in an encapsulant (Block **730**) using, for example, injection molding or other suitable encasing techniques.

Any one of the semiconductor components described above with reference to FIGS. **1** and **3-5** can be incorporated into any of a myriad of larger and/or more complex systems, a representative example of which is system **800** shown schematically in FIG. **8**. The system **800** can include a processor **801**, a memory **802** (e.g., SRAM, DRAM, flash, and/or other memory device), input/output devices **803**, and/or other subsystems or components **804**. The foregoing semiconductor components described above with reference to FIGS. **1** and **3-5** can be included in any of the components shown in FIG. **8**. The resulting system **800** can perform any of a wide variety of computing, processing, storage, sensing, imaging, and/or other functions. Accordingly, representative systems **800**

include, without limitation, computers and/or other data processors, for example, desktop computers, laptop computers, internet appliances, hand-held devices (e.g., palm-top computers, wearable computers, cellular or mobile phones, personal digital assistants, etc), multi-processor systems, processor-based or programmable consumer electronics, network computers, and mini computers. Other representative systems **800** include cameras, light or other radiation sensors, servers and associated server subsystems, display devices, and/or other memory devices. In such systems, individual dies can include imager arrays, such as CMOS imagers. Components of the system **800** can be housed in a single unit or distributed over multiple, interconnected units (e.g., through a communications network). The components of the system **800** can accordingly include local and/or remote memory storage devices, and any of a wide variety of computer readable media.

From the foregoing, it will be appreciated that specific embodiments of the invention have been described herein for purposes of illustration, but that various modifications can be made without deviating from the inventions. For example, the packaged semiconductor component **100** in FIG. **3** can include an additional support member that is attached to the second surface **105b** of the die **102**. Certain aspects of the invention described in the context of particular embodiments may be combined or eliminated in other embodiments. For example, the packaged semiconductor packages described with reference to FIGS. **1**, **3**, and **4** can also include more than one dies attached to one or more support members. Additionally, where the context permits, singular or plural terms can also include plural or singular terms, respectively. Moreover, unless the word “or” is expressly limited to mean only a single item exclusive from the other items in reference to a list of two or more items, then the use of “or” in such a list means including (a) any single item in the list, (b) all of the items in the list, or (c) any combination of the items in the list. Additionally, the term “comprising” is used throughout the following disclosure to mean including at least the recited feature(s) such that any greater number of the same feature and/or additional types of features or components is not precluded. Further, while advantages associated with certain embodiments of the invention have been described in the context of those embodiments, other embodiments may also exhibit such advantages, and not all embodiments need necessarily exhibit such advantages to fall within the scope of the invention. Accordingly, the invention is not limited, except as by the appended claims.

We claim:

1. A packaged semiconductor component, comprising:
 - a semiconductor die having a bond pad, a first composition, and a first width;
 - a support member proximate to the semiconductor die, the support member being at least substantially rigid and having a second width generally equal to the first width and a second composition different from the first composition of the semiconductor die, wherein the support member includes a first plate, a second plate, and a plurality of heat conducting fins between the first and second plates;
 - a first adhesive attaching the semiconductor die to the support member;
 - a substrate having a connection site and carrying the semiconductor die and the support member attached to the semiconductor die;
 - a second adhesive attaching the support member to the substrate;

a wirebond extending between the bond pad of the semiconductor die and the connection site of the substrate; and

an encapsulant at least partially encasing the semiconductor die, the support member, the first adhesive, the second adhesive, the wirebond, and the substrate.

2. The packaged semiconductor component of claim 1 wherein the support member is a plate constructed from at least one of a metal, a metal alloy, ceramics, polymers, and glass.

3. The packaged semiconductor component of claim 1 wherein the support member is a laminated structure having one at least substantially rigid layer.

4. The packaged semiconductor component of claim 1 wherein the semiconductor die further includes an array of photo sensors positioned at or near the a surface of the semiconductor die.

5. The packaged semiconductor component of claim 4, further comprising a glass member disposed adjacent to the array of photo sensors positioned at or near the surface of the semiconductor die.

6. The packaged semiconductor component of claim 1 wherein the support member and the first adhesive are preformed into a die attach film.

7. The packaged semiconductor component of claim 1 wherein the semiconductor die has a first surface and a second surface opposite the first surface, and wherein the bond pad is located on or near the first surface, and wherein the support member is attached to the second surface of the semiconductor die.

8. A packaged semiconductor component, comprising:

- a semiconductor die having a bond pad at a first die surface and a second die surface opposite the first die surface, the semiconductor die having a first width;

a support member proximate to the semiconductor die, the support member including a plate having a second width generally equal to the first width and constructed from a metal and/or a metal alloy and having a composition different from a composition of the semiconductor die, wherein the support member includes a first plate, a second plate, and a plurality of heat conducting fins between the first and second plates;

a first adhesive directly between the second die surface of the semiconductor die and the support member;

a substrate having a connection site at a first substrate surface and a second substrate surface opposite the first substrate surface;

a second adhesive directly between the support member and the first substrate surface of the substrate;

a wirebond extending between the bond pad of the semiconductor die and the connection site of the substrate;

an encapsulant at least partially encasing the semiconductor die, the support member, the first adhesive, the second adhesive, the wirebond, and the substrate; and

a plurality of solder balls attached to the second substrate surface of the substrate.

9. The packaged semiconductor component of claim 8 wherein the support member does not include a semiconductor die.

10. The packaged semiconductor component of claim 8 wherein the support member has a rigidity sufficient to at least partially resist flexing during thermal cycling.

11. The packaged semiconductor component of claim 8 wherein the support member has a heat conductivity sufficient to at least partially equalize heat transfer from the semiconductor die during operation.

9

12. The packaged semiconductor component of claim 8 wherein the support member has a thickness of about 100 microns to about 3 mm.

13. A packaged semiconductor component, comprising:
 a semiconductor die having a plurality of bond pads at a
 first die surface and a second die surface opposite the
 first die surface, the semiconductor die having a first
 width;
 a substantially rigid plate proximate to the semiconductor
 die, the plate having a first plate surface proximate to the
 semiconductor die and a second plate surface opposite
 the first plate surface, the plate having a second width
 generally equal to the first width and a thickness of about
 100 microns to about 3 mm, the plate being constructed
 from at least one of a metal, a metal alloy, ceramics,
 polymers, and glass, wherein the plate includes a first
 plate, a second plate, and a plurality of heat conducting
 fins between the first and second plates;
 a first adhesive directly between the first plate surface of the
 plate and the second die surface of the semiconductor
 die;
 a substrate carrying the semiconductor die and the plate,
 the substrate having a plurality of connection sites at a
 first substrate surface and a second substrate surface
 opposite the first substrate surface, the substrate having
 a third width larger than the first and second widths;

10

a second adhesive directly between the second plate sur-
 face of the plate and the first substrate surface of the
 substrate;
 a plurality of wirebonds individually extending between
 the bond pads of the semiconductor die and the connec-
 tion sites of the substrate;
 an encapsulant at least partially encapsulating the semicon-
 ductor die, the plate, the first adhesive, the second adhe-
 sive, the wirebonds, and the substrate; and
 a plurality of solder balls attached to the second substrate
 surface of the substrate.

14. The packaged semiconductor component of claim 13 wherein the semiconductor die further includes an array of photo sensors positioned at or near the first die surface of the semiconductor die.

15. The packaged semiconductor component of claim 13 wherein the semiconductor die further includes an array of photo sensors positioned at or near the first surface of the semiconductor die, and wherein the encapsulant includes an opening generally corresponding to the array of photo sensors, and further wherein the packaged semiconductor component includes a glass member in the opening of the encapsulant and adjacent to the array of photo sensors positioned at or near the first die surface of the semiconductor die.

* * * * *

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

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INVENTOR(S) : Matt E. Schwab et al.

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In column 8, line 16, in Claim 4, delete “the a” and insert -- the --, therefor.

Signed and Sealed this

Thirty-first Day of August, 2010

A handwritten signature in black ink that reads "David J. Kappos". The signature is written in a cursive style with a large, prominent 'D' and 'K'.

David J. Kappos
Director of the United States Patent and Trademark Office